L Number	******		DB	Time stamp
-	1515	Jane meditation (recessive groovs) meditation	USPAT;	2003/12/03 18:14
		substrate	US-PGPUB	2003/12/03 18.19
-	119		USPAT;	2003/12/03 18:14
		substrate) and ((silicon near3 germanium)	US-PGPUB	2003/12/03 18:14
		S1?Ge Si-Ge SiGe)	05-FGFUB	
-	24755	((silicon near3 germanium) Si?Ge Si-Ge SiGe)	USPAT;	0000/00/00
		5 5100 51 00 5100		2003/12/03 18:14
-	8216	gate near100 (reces\$4 groov\$3 open\$4 trench)	US-PGPUB	
-		near100 substrate	USPAT;	2003/12/03 18:14
	19782		US-PGPUB	
	1	same substrate	USPAT;	2003/12/03 18:15
_	8237		US-PGPUB	
	0237	with substrate	USPAT;	2003/12/03 18:15
	19782		US-PGPUB	
	15702		USPAT;	2003/12/03 18:15
	ĺ	trench) near100 substrate) (gate same	US-PGPUB	, ,, ,, ,,
		(reces\$4 groov\$3 open\$4 trench) same		
		substrate) (gate with (reces\$4 groov\$3		
		open\$4 trench) with substrate)		
	1619	(((silicon near3 germanium) Si?Ge Si-Ge	USPAT;	2002/12/02 10 16
		SiGe)) and ((gate near100 (recess4 groups	US-PGPUB	2003/12/03 18:16
		Open54 trench) near100 substrate) (gate same	05-FGFUB	İ
		(recess4 groovs3 opens4 trench) same		
		substrate) (gate with (reces\$4 groov\$3		
		open\$4 trench) with substrate))		
-	4	(("6214679") or ("5624869") or ("5883003")	1	
1		or ("6037922")).PN.	USPAT;	2003/12/04 10:03
-	45	"6214679"	US-PGPUB	
		"5624869."	USPAT;	2003/12/04 10:03
		"5883003"	US-PGPUB	
		"6037922"		1
	1623			
	1023	(((silicon near3 germanium) Si?Ge Si-Ge	USPAT;	2003/12/04 10:22
	I	Side)) and ((gate nearing (recess) groups)	US-PGPUB	10.22
	1	open\$4 trench) near100 substrate) (gate game		
	1	(recess4 groovs3 opens4 trench) came		
		substrate) (gate with (recess4 groovs)		
		open\$4 trench) with substrate))		
}	38	(((silicon near3 germanium) Si?Ge Si-Ge	EDO. TOO	2002/20/2
	1	SiGe)) and ((gate near100 (recess) groups)	EPO; JPO;	2003/12/04 10:23
		open\$4 trench) near100 substrate) (gate same	DERWENT;	1
		(reces\$4 groov\$3 open\$4 trench) same	IBM_TDB	l
		substrate) (gate with (reces\$4 groov\$3		
		open\$4 trench) with substrate))		
.		opony: crement/ with substrate))		
	653	anisotroniase normanist to		
	033	anisotropic\$6 near100 etch\$3 near100	EPO; JPO;	2003/12/04 11:20
		(substrate wafer) near100 gate	DERWENT;	1,, 51 12.20
	. 0	(and and the state of the state	IBM_TDB	
	U	(anisotropic\$6 near100 etch\$3 near100	EPO; JPO;	000011-
	* 1	/	EPO; dPO:	2003/19/04 11.45
	1	(substrate wafer) near100 gate) and ((silicon near3 germanium) Si-Ge Si?Ge SiGe)	DERWENT;	2003/12/04 11:19